**Product data sheet** 

## 1. General description

Planar passivated four quadrant triac in a SOT186A (TO-220F) plastic package intended for use in applications requiring high bidirectional transient and blocking voltage capability and high thermal cycling performance. Typical applications include motor control, industrial and domestic lighting, heating and static switching.

### 2. Features and benefits

- · High blocking voltage capability
- · Planar passivated for voltage ruggedness and reliability
- · Less sensitive gate for improved noise immunity
- · Triggering in all four quadrants
- Isolated package

### 3. Applications

- General purpose motor control
- General purpose switching

### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions	Values			Unit
Absolute	maximum rating					
$V_{DRM}$	repetitive peak off-state voltage			600		V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; T <sub>h</sub> ≤ 38 °C; Fig. 1; Fig. 2; Fig. 3	16		А	
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 20 ms; Fig. 4; Fig. 5	155		А	
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics					
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G+;$ $T_j = 25 \text{ °C; } Fig. 7$	-	5	25	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2+ G-;}$ $T_j = 25 \text{ °C; Fig. 7}$	-	8	25	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G-;}$ $T_j = 25 \text{ °C; } Fig. 7$	-	10	25	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G+;}$ $T_j = 25 \text{ °C; } Fig. 7$	-	22	70	mA

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# 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	
2	T2	main terminal 2		N
3	G	gate		T2 T1
mb	n.c.	mounting base; isolated		sym051

# 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package				
	Name	Description	Version		
BT139X-600F	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A		

# 7. Marking

### **Table 4. Marking codes**

Type number	Marking codes
BT139X-600F	BT139X-600F

**4Q Triac** 

# 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
$V_{DRM}$	repetitive peak off-state voltage		600	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_h \le 38 ^{\circ}\text{C}$ ; Fig 1; Fig 2; Fig 3	16	А
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 20 ms; Fig 4; Fig 5	155	А
		full sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 16.7 ms	170	Α
l <sup>2</sup> t	I <sup>2</sup> t for fusing	t <sub>p</sub> = 10 ms; SIN	120	A <sup>2</sup> s
dl <sub>⊤</sub> /dt	rate of rise of on-state	I <sub>G</sub> = 50 mA; T2+ G+	50	A/µs
	current	I <sub>G</sub> = 50 mA; T2+ G-	50	A/µs
		I <sub>G</sub> = 50 mA; T2- G-	50	A/µs
		I <sub>G</sub> = 140 mA; T2- G+	10	A/µs
I <sub>GM</sub>	peak gate current		2	А
$P_{GM}$	peak gate power		5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	0.5	W
T <sub>stg</sub>	storage temperature		-40 to 150	°C
T <sub>j</sub>	junction temperature		125	°C

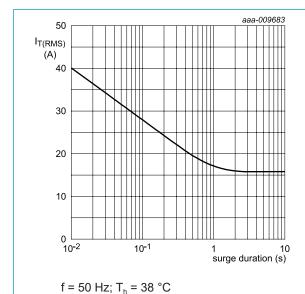


Fig. 1. RMS on-state current as a function of surge duration; maximum values

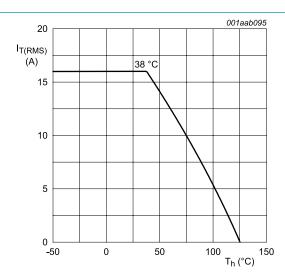
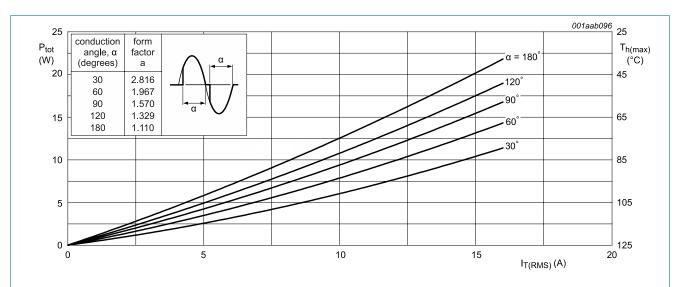


Fig. 2. RMS on-state current as a function of heatsink temperature; maximum values

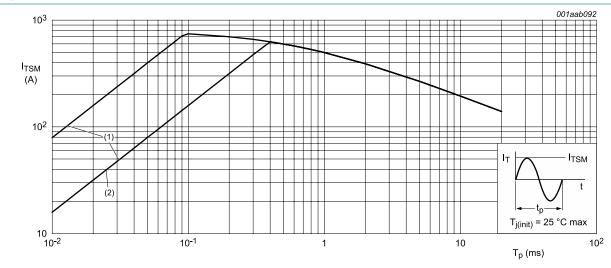
**4Q Triac** 



 $\alpha$  = conduction angle

a = form factor =  $I_{T(RMS)} / I_{T(AV)}$ 

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values



t<sub>p</sub> ≤ 20 ms

- $(1) dI_{T}/dt limit$
- (2) T2- G+ quadrant limit

Fig. 4. Non-repetitive peak on-state current as a function of pulse width; maximum values

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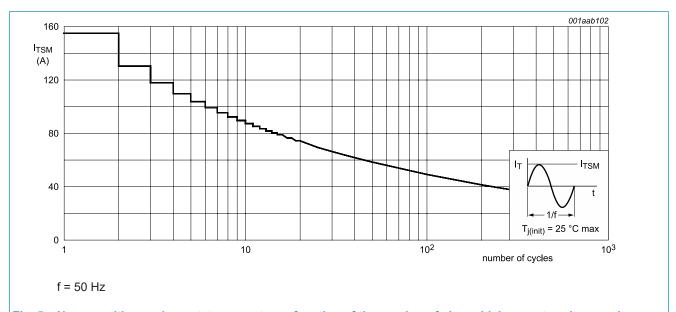


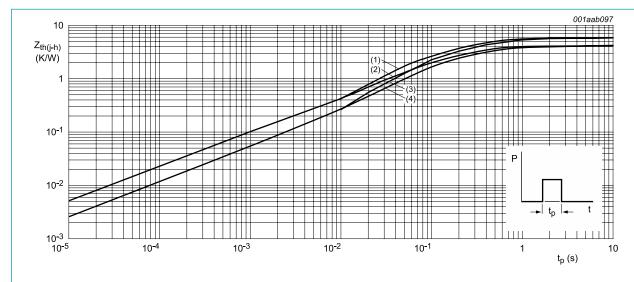
Fig. 5. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to	full or half cycle; with heatsink compound; Fig 6	-	-	4	K/W
hea	heatsink	full or half cycle; without heatsink compound; Fig 6	-	-	5.5	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	-	55	-	K/W



- (1) Unidirectional (half cycle) without heatsink compound
- (2) Unidirectional (half cycle) with heatsink compound
- (3) Bidirectional (full cycle) without heatsink compound
- (4) Bidirectional (full cycle) with heatsink compound

Fig. 6. Transient thermal impedance from junction to heatsink as a function of pulse width

### 10. Isolation characteristics

Table 7. Isolation characteristics

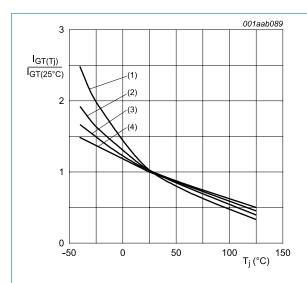
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>isol(RMS)</sub>	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free; 50 Hz $\leq$ f $\leq$ 60 Hz; RH $\leq$ 65 %; $T_h = 25$ °C	-	-	2500	V
C <sub>isol</sub>	isolation capacitance	from main terminal 2 to external heatsink; f = 1 MHz; T <sub>h</sub> = 25 °C	-	10	-	pF

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## 11. Characteristics

**Table 8. Characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 7$	-	5	25	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 \text{ °C}; Fig. 7$	-	8	25	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{G-};$ $T_j = 25 \text{ °C}; Fig. 7$	-	10	25	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- G+;$ $T_j = 25 \text{ °C}; Fig. 7$	-	22	70	mA
I <sub>L</sub> la	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 8$	-	7	40	mA
		$V_D = 12 \text{ V; } I_G = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; } Fig. 8$	-	20	60	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 8}}$	-	8	40	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 8}}$	-	10	60	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	6	45	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 20 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1.2	1.6	V
V <sub>GT</sub>	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	0.7	1	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 ^{\circ}\text{C};$ Fig. 11	0.25	0.4	-	V
$I_D$	off-state current	V <sub>D</sub> = 600 V; T <sub>j</sub> = 125 °C	-	0.1	0.5	mA
Dynamic	characteristics					
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 402 V; $T_j$ = 125 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit	50	250	-	V/µs
dV <sub>com</sub> /dt	rate of change of commutating voltage	$V_D$ = 400 V; $T_j$ = 95 °C; $dI_{com}/dt$ = 7.2 A/ms; $I_T$ = 16 A; gate open circuit	-	20	-	V/µs
$\mathbf{t}_{\mathrm{gt}}$	gate-controlled turn-on time	$V_D = 600 \text{ V}; I_{TM} = 20 \text{ A}; I_G = 0.1 \text{ A};$ $dI_G/dt = 5 \text{ A}/\mu\text{s}$	-	2	-	μs



- (1) T2- G+
- (2) T2- G-
- (3) T2+ G-
- (4) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

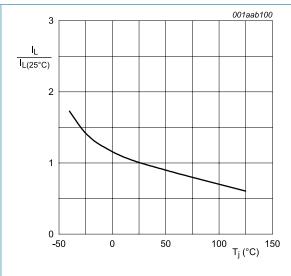


Fig. 8. Normalized latching current as a function of junction temperature

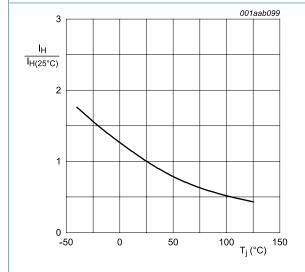
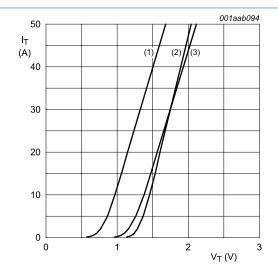


Fig. 9. Normalized holding current as a function of junction temperature

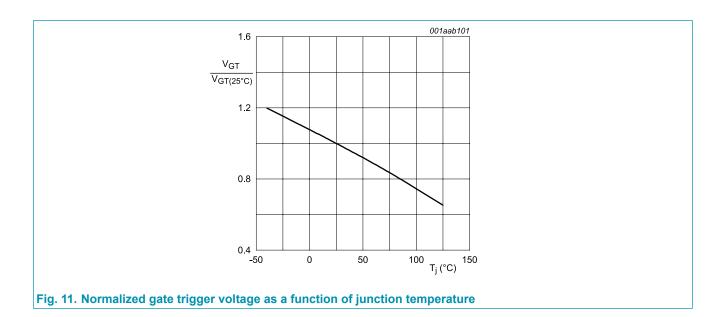


- $V_o$  = 1.195 V;  $R_s$  = 0.018 Ω (1)  $T_j$  = 125 °C; typical values (2)  $T_j$  = 125 °C; maximum values
- (3) T<sub>i</sub> = 25 °C; maximum values

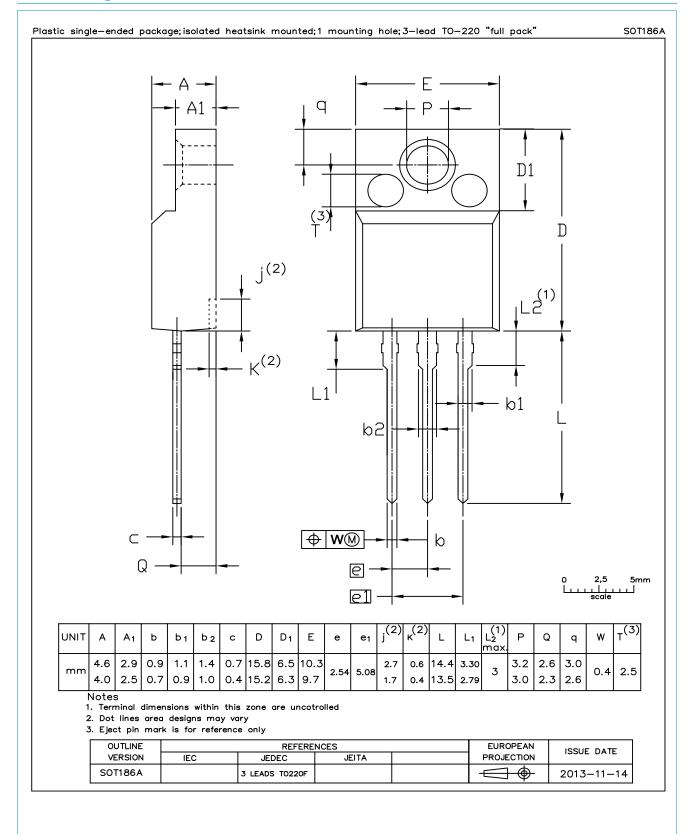
Fig. 10. On-state current as a function of on-state voltage

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# 12. Package outline



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### 13. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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For more information, please visit: http://www.ween-semi.com
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Тел: +7 (812) 336 43 04 (многоканальный) Email: org@lifeelectronics.ru